# HEF4067B-Q100

# 16-channel analog multiplexer/demultiplexer Rev. 1 — 24 September 2013

**Product data sheet** 

#### **General description** 1.

The HEF4067B-Q100 is a 16-channel analog multiplexer/demultiplexer. It has four address inputs (A0 to A3), an active LOW enable input (E), 16 independent inputs/outputs (Y0 to Y15) and a common input/output (Z). The device contains 16 bidirectional analog switches. Each switch has one side connected to an independent input/output (Y0 to Y15) and the other side connected to the common input/output (Z). With E LOW, one of the 16 switches is selected (low-impedance ON-state) by A0 to A3. All unselected switches are in the high-impedance OFF-state. With E HIGH all switches are in the high-impedance OFF-state, independent of A0 to A3. The analog inputs/outputs (Y0 to Y15 and Z) can swing between  $V_{DD}$  as a positive limit and  $V_{SS}$  as a negative limit.  $V_{DD}$  to V<sub>SS</sub> may not exceed 15 V.

This product has been qualified to the Automotive Electronics Council (AEC) standard Q100 (Grade 3) and is suitable for use in automotive applications.

#### **Features and benefits** 2.

- Automotive product qualification in accordance with AEC-Q100 (Grade 3)
  - ◆ Specified from -40 °C to +85 °C
- Fully static operation
- 5 V, 10 V, and 15 V parametric ratings
- Standardized symmetrical output characteristics
- ESD protection:
  - MIL-STD-883, method 3015 exceeds 2000 V
  - HBM JESD22-A114F exceeds 2000 V
  - MM JESD22-A115-A exceeds 200 V (C = 200 pF, R = 0 Ω)
- Complies with JEDEC standard JESD 13-B

# **Applications**

- Analog multiplexing and demultiplexing
- Digital multiplexing and demultiplexing
- Signal gating

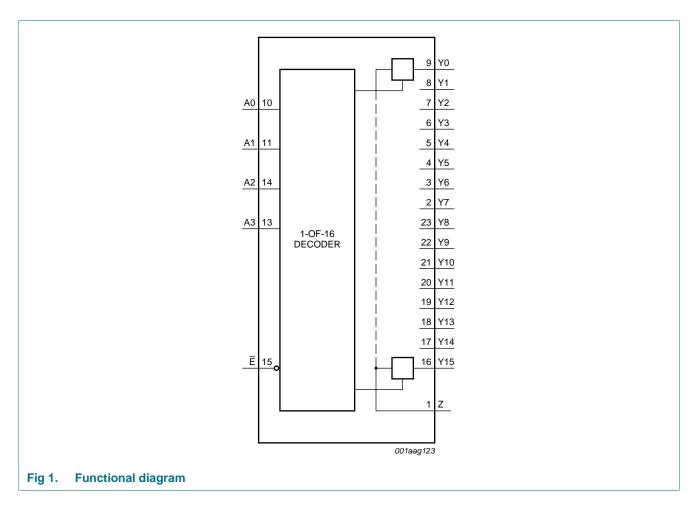


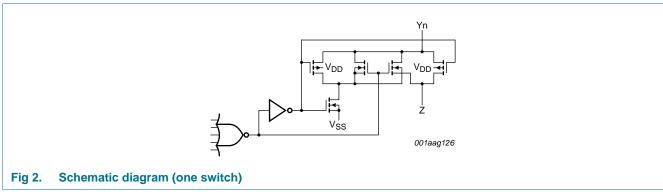
# 4. Ordering information

Table 1. Ordering information

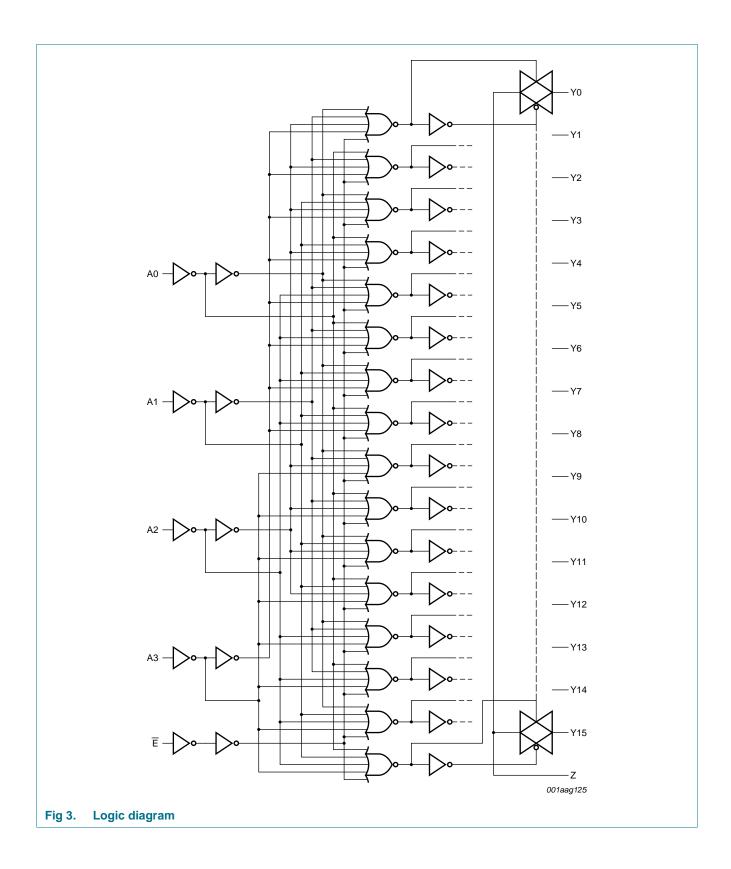
Type number	Package	ckage										
	Temperature range	Name	Description	Version								
HEF4067BT-Q100	–40 °C to +85 °C	SO24	plastic small outline package; 24 leads; body width 7.5 mm	SOT137-1								

# 5. Functional diagram



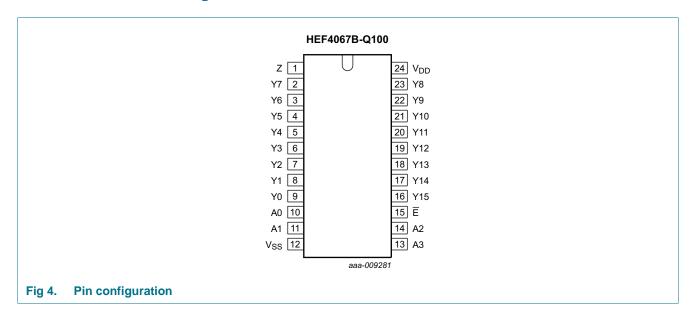


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# 6. Pinning information

## 6.1 Pinning



## 6.2 Pin description

Table 2. Pin description

Symbol	Pin	Description
Z	1	common input/output
Y0 to Y15	9, 8, 7, 6, 5, 4, 3, 2, 23, 22, 21, 20, 19, 18, 17, 16	independent input/output
A0 to A3	10, 11, 14, 13	address input
$V_{SS}$	12	ground (0 V)
Ē	15	enable input (active LOW)
$V_{DD}$	24	supply voltage

# 7. Functional description

Table 3. Function table[1]

Control	Address			Channel ON	
E	A3	A2	A1	Α0	
L	L	L	L	L	Y0 = Z
L	L	L	L	Н	Y1 = Z
L	L	L	Н	L	Y2 = Z
L	L	L	Н	Н	Y3 = Z
L	L	Н	L	L	Y4 = Z
L	L	Н	L	Н	Y5 = Z
L	L	Н	Н	L	Y6 = Z
L	L	Н	Н	Н	Y7 = Z
L	Н	L	L	L	Y8 = Z
L	Н	L	L	Н	Y9 = Z
L	Н	L	Н	L	Y10 = Z
L	Н	L	Н	Н	Y11 = Z
L	Н	Н	L	L	Y12 = Z
L	Н	Н	L	Н	Y13 = Z
L	Н	Н	Н	L	Y14 = Z
L	Н	Н	Н	Н	Y15 = Z
Н	X	Χ	Х	Х	none

<sup>[1]</sup> H = HIGH voltage level; L = LOW voltage level; X = don't care.

# 8. Limiting values

Table 4. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134). Voltages are referenced to  $V_{SS} = 0 \text{ V}$  (ground).

Symbol	Parameter	Conditions	Min	Max	Unit
$V_{DD}$	supply voltage		-0.5	+18	V
I <sub>IK</sub>	input clamping current	pins An and $\overline{E}$ ; V <sub>I</sub> < -0.5 V or V <sub>I</sub> > V <sub>DD</sub> + 0.5 V	-	±10	mA
VI	input voltage		-0.5	$V_{DD} + 0.5$	V
I <sub>I/O</sub>	input/output current		<u>[1]</u> -	±10	mA
I <sub>DD</sub>	supply current		-	50	mA
T <sub>stg</sub>	storage temperature		-65	+150	°C
T <sub>amb</sub>	ambient temperature		-40	+85	°C
P <sub>tot</sub>	total power dissipation	$T_{amb} = -40  ^{\circ}\text{C} \text{ to } +125  ^{\circ}\text{C}$	[2] -	500	mW
Р	power dissipation	per output	-	100	mW

<sup>[1]</sup> To avoid drawing V<sub>DD</sub> current from terminal Z, when switch current flows into terminals Yn, the voltage drop across the bidirectional switch must not exceed 0.4 V. If the switch current flows into terminal Z, no V<sub>DD</sub> current flows from terminals Yn. In this case, there is no limit for the voltage drop across the switch, but the voltages at Y and Z may not exceed V<sub>DD</sub> or V<sub>SS</sub>.

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<sup>[2]</sup> For SO24 packages: above  $T_{amb}$  = 70 °C,  $P_{tot}$  derates linearly at 8 mW/K.

# 9. Recommended operating conditions

Table 5. Recommended operating conditions

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
$V_{DD}$	supply voltage		3	-	15	V
VI	input voltage		0	-	$V_{DD}$	V
T <sub>amb</sub>	ambient temperature	in free air	-40	-	+85	°C
Δt/ΔV	input transition rise and fall rate	$V_{DD} = 5 V$	-	-	3.75	μs/V
		$V_{DD} = 10 \text{ V}$	-	-	0.5	μs/V
		$V_{DD} = 15 \text{ V}$	-	-	0.08	μs/V

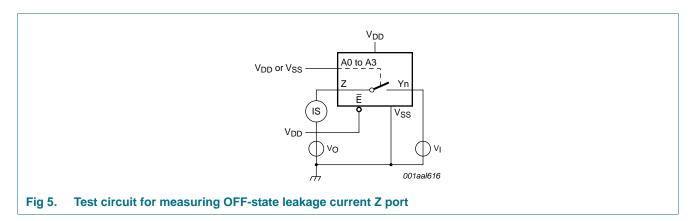
# 10. Static characteristics

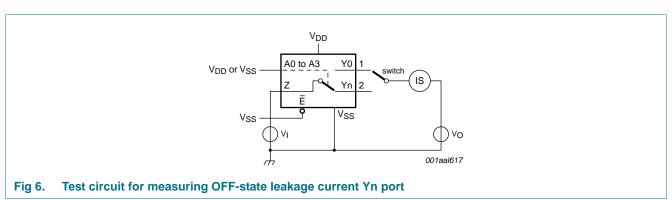
#### Table 6. Static characteristics

 $V_{SS} = 0$  V;  $V_I = V_{SS}$  or  $V_{DD}$ ; unless otherwise specified.

Symbol	Parameter	Conditions	$V_{DD}$	T <sub>amb</sub> =	-40 °C	T <sub>amb</sub> =	+25 °C	T <sub>amb</sub> =	+85 °C	Unit
				Min	Max	Min	Max	Min	Max	
$V_{IL}$	LOW-level input	I <sub>O</sub>   < 1 μA								
	voltage	$V_0 = 0.5 \text{ V or } 4.5 \text{ V}$	5 V	-	1	-	1	-	1	V
		$V_0 = 1.0 \text{ V or } 9.0 \text{ V}$	10 V	-	2	-	2	-	2	V
		V <sub>O</sub> = 1.5 V or 13.5 V	15 V	-	2.5	-	2.5	-	2.5	V
$V_{IH}$	HIGH-level input	I <sub>O</sub>   < 1 μA								
	voltage	$V_0 = 0.5 \text{ V or } 4.5 \text{ V}$	5 V	4	-	4	-	4	-	V
	$V_0 = 1.0 \text{ V or } 9.0 \text{ V}$	10 V	8	-	8	-	8	-	V	
		$V_0 = 1.5 \text{ V or } 13.5 \text{ V}$	15 V	12.5	-	12.5	-	12.5	-	V
I <sub>I</sub>	input leakage current	$V_I = 0 \text{ V or } 15 \text{ V}$	15 V	-	±0.3	-	±0.3	-	±1.0	μΑ
l <sub>OZ</sub>	OFF-state output	output at V <sub>DD</sub>	15 V	-	1.6	-	1.6	-	12.0	μΑ
	current	output at V <sub>SS</sub>	15 V	-	-1.6	-	-1.6	-	-12.0	μΑ
I <sub>S(OFF)</sub>	OFF-state leakage current	Z port; all channels OFF; see Figure 5	15 V	-	-	-	1000	-	-	nA
		Yn port; per channel; see Figure 6	15 V	-	-	-	200	-	-	nA
I <sub>DD</sub>	supply current	all valid input combinations;	5 V	-	20	-	20	-	150	μΑ
		$I_O = 0 A$	10 V	-	40	-	40	-	300	μΑ
			15 V	-	80	-	80	-	600	μΑ
Cı	input capacitance	digital inputs	15 V	-	-	-	7.5	-	-	рF

## 10.1 Test circuits





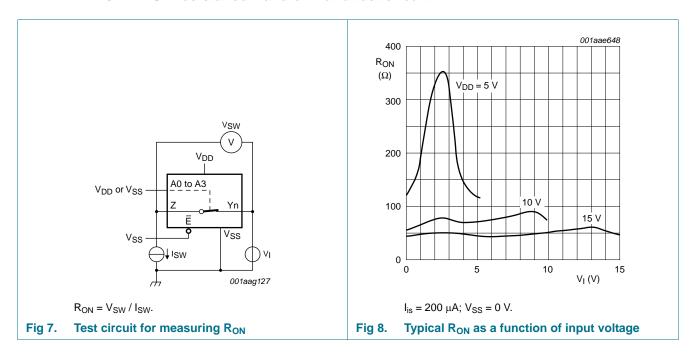
#### 10.2 On resistance

Table 7. ON resistance

 $T_{amb} = 25$  °C;  $I_{SW} = 200~\mu A$ ;  $V_{SS} = 0~V$ .

Symbol	Parameter	Conditions	$V_{DD}$	Тур	Max	Unit
R <sub>ON(peak)</sub>	ON resistance (peak)	$V_I = 0 \text{ V to } V_{DD}$ ; see <u>Figure 7</u> and	5 V	350	2500	Ω
		Figure 8	10 V	80	245	Ω
			15 V	60	175	Ω
R <sub>ON(rail)</sub>	ON resistance (rail)	V <sub>I</sub> = 0 V; see <u>Figure 7</u> and <u>Figure 8</u>	5 V	115	340	Ω
			10 V	50	160	Ω
			15 V	40	115	Ω
		$V_I = V_{DD}$ ; see Figure 7 and Figure 8	5 V	120	365	Ω
			10 V	65	200	Ω
			15 V	50	155	Ω
$\Delta R_{ON}$	ON resistance mismatch	$V_I = 0 \text{ V to } V_{DD}$ ; see <u>Figure 7</u>	5 V	25	-	Ω
	between channels		10 V	10	-	Ω
			15 V	5	-	Ω

## 10.2.1 On resistance waveform and test circuit



# 11. Dynamic characteristics

Table 8. Dynamic characteristics

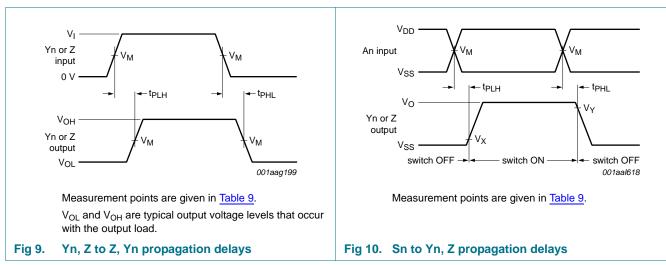
 $T_{amb} = 25$  °C;  $V_{SS} = 0$  V; for test circuit, see <u>Figure 12</u>.

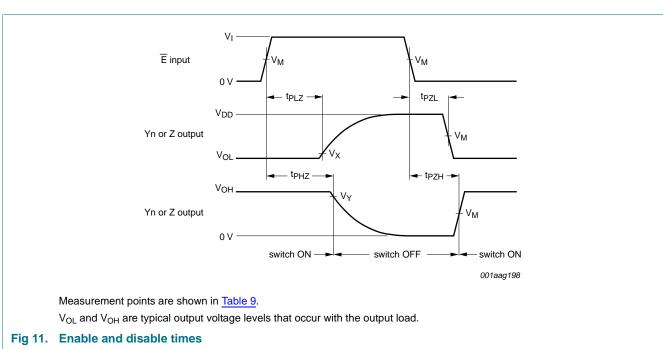
Symbol	Parameter	Conditions	$V_{DD}$	Min	Тур	Max	Unit
t <sub>PHL</sub>	HIGH to LOW propagation delay	Yn, Z to Z, Yn; see Figure 9	5 V	-	30	60	ns
			10 V	-	15	25	ns
			15 V	-	10	20	ns
		An to Yn, Z; see Figure 10	5 V	-	190	380	ns
			10 V	-	70	145	ns
			15 V	-	50	100	ns
t <sub>PLH</sub>	LOW to HIGH propagation delay		5 V	-	25	50	ns
			10 V	-	10	20	ns
			15 V	-	10	20	ns
		An to Yn, Z; see Figure 10	5 V	-	175	345	ns
			10 V	-	70	140	ns
			15 V	-	50	100	ns
t <sub>PHZ</sub>	HIGH to OFF-state propagation delay	E to Yn, Z; see Figure 11	5 V	-	195	385	ns
			10 V	-	140	280	ns
			15 V	-	130	260	ns
t <sub>PLZ</sub>	LOW to OFF-state propagation delay	E to Yn, Z; see Figure 11	5 V	-	215	435	ns
			10 V	-	180	355	ns
			15 V	-	170	340	ns

**Table 8. Dynamic characteristics** ...continued  $T_{amb} = 25 \, ^{\circ}\text{C}$ ;  $V_{SS} = 0 \, \text{V}$ ; for test circuit, see <u>Figure 12</u>.

Symbol	Parameter	Conditions	$V_{DD}$	Min	Тур	Max	Unit
t <sub>PZH</sub>	OFF-state to HIGH propagation delay	E to Yn, Z; see Figure 11	5 V	-	155	315	ns
			10 V	-	70	135	ns
		E to Yn, Z; see Figure 11	15 V	-	50	100	ns
t <sub>PZL</sub>	OFF-state to LOW propagation delay		5 V	-	170	340	ns
			10 V	-	70	140	ns
			15 V	-	50	100	ns

#### 11.1 Waveforms and test circuit





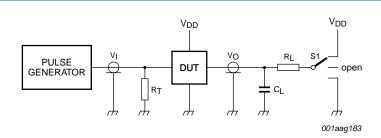
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Table 9. Measurement points

Supply voltage	Input		Output				
V <sub>CC</sub>	V <sub>M</sub>	VI	V <sub>M</sub>	V <sub>X</sub>	V <sub>Y</sub>		
5 V to 15 V	$0.5V_{DD}$	GND to V <sub>DD</sub>	$0.5V_{DD}$	10%	90%		



Test data is given in Table 10.

Definitions test circuit:

 $R_T$  = termination resistance should be equal to output impedance  $Z_0$  of the pulse generator

C<sub>L</sub> = load capacitance including jig and probe capacitance

R<sub>L</sub> = load resistor

S1 = test selection switch

Fig 12. Test circuit for measuring switching times

Table 10. Test data

Input Lo			Load		S1 position	ı				
Yn, Z	An and E	t <sub>r</sub> , t <sub>f</sub>	V <sub>M</sub>	C <sub>L</sub>	$R_L$	t <sub>PHL</sub> [1]	t <sub>PLH</sub>	$t_{PZH},t_{PHZ}$	$t_{PZL}, t_{PLZ}$	other
$V_{DD}$ or $V_{SS}$	$V_{DD}$ or $V_{SS}$	≤ 20 ns	$0.5V_{DD}$	50 pF	10 k $\Omega$	$V_{DD}$ or $V_{SS}$	$V_{SS}$	$V_{SS}$	$V_{DD}$	$V_{SS}$

[1] For Yn to Z or Z to Yn propagation delays, use  $V_{SS}$ . For An or to Yn or Z propagation delays, use  $V_{DD}$ .

# 11.2 Additional dynamic parameters

Table 11. Additional dynamic characteristics

 $V_{SS} = 0$  V;  $T_{amb} = 25$  °C.

Symbol	Parameter	Conditions	$V_{DD}$	Тур	Max	Unit
THD	total harmonic distortion	see Figure 13; $R_L = 10 \text{ k}\Omega$ ; $C_L = 15 \text{ pF}$ ;	5 V	[ <u>1</u> ] 0.25	-	%
		channel ON; $V_I = 0.5V_{DD}$ (p-p); $f_i = 1$ kHz	10 V	<u>[1]</u> 0.04	-	%
		$I_{i} = I \text{ K} I Z$	15 V	<u>[1]</u> 0.04	-	%
f <sub>(-3dB)</sub>	-3 dB frequency response	see Figure 14; $R_L = 1 \text{ k}\Omega$ ; $C_L = 5 \text{ pF}$ ;	5 V	<u>[1]</u> 13	-	MHz
		channel ON; $V_I = 0.5V_{DD}$ (p-p)	10 V	<u>[1]</u> 40	-	MHz
			15 V	<u>[1]</u> 70	-	MHz
$\alpha_{\text{iso}}$	isolation (OFF-state)	see Figure 15; $f_i$ = 1 MHz; $R_L$ = 1 $k\Omega$ ; $C_L$ = 5 pF; channel OFF; $V_I$ = 0.5 $V_{DD}$ (p-p)	10 V	<u>[1]</u> –50	-	dB
V <sub>ct</sub>	crosstalk voltage	digital inputs to switch; see Figure 16; $\underline{R}_L = 10 \text{ k}\Omega$ ; $C_L = 15 \text{ pF}$ ; $\overline{E}$ or $An = V_{DD}$ (square-wave)	10 V	50	-	mV
Xtalk	crosstalk	between switches; see Figure 17; $f_i = 1$ MHz; $R_L = 1$ k $\Omega$ ; $V_I = 0.5V_{DD}$ (p-p)	10 V	<u>[1]</u> –50	-	dB

<sup>[1]</sup>  $f_i$  is biased at 0.5  $V_{DD}$ ;  $V_I = 0.5 V_{DD}$  (p-p).

## Table 12. Dynamic power dissipation P<sub>D</sub>

 $P_D$  can be calculated from the formulas shown;  $V_{SS} = 0$  V;  $t_r = t_f \le 20$  ns;  $T_{amb} = 25$  °C.

<i>D</i>			/ 00 - / 1/ umb	
Symbol	Parameter	$V_{DD}$	Typical formula for $P_D$ ( $\mu$ W)	where:
$P_D$	dynamic power	5 V	$P_D = 1000 \times f_i + \Sigma (f_o \times C_L) \times V_{DD}^2$	f <sub>i</sub> = input frequency in MHz;
	dissipation	ion 10 V	$P_D = 5500 \times f_i + \Sigma (f_o \times C_L) \times V_{DD}^2$	f <sub>o</sub> = output frequency in MHz;
		15 V	$P_D = 15000 \times f_i + \Sigma (f_o \times C_L) \times V_{DD}^2$	$C_L$ = output load capacitance in pF;
				$V_{DD}$ = supply voltage in V;
				$\Sigma(C_L \times f_o)$ = sum of the outputs.

#### 11.2.1 Test circuits

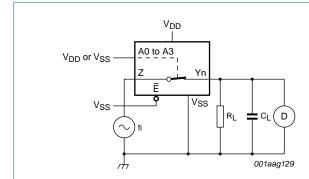


Fig 13. Test circuit for measuring total harmonic distortion

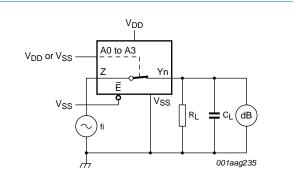
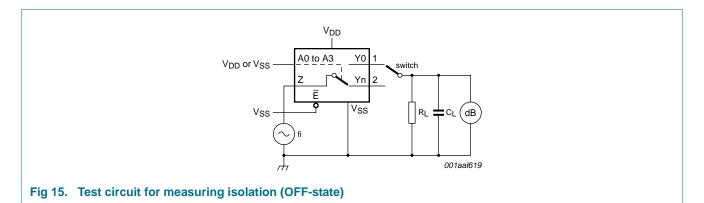
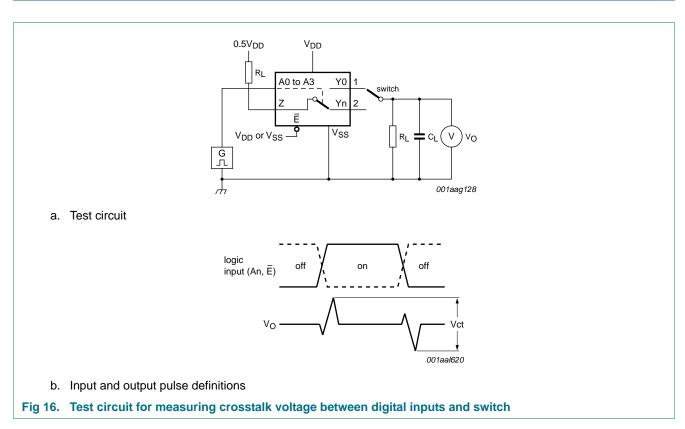
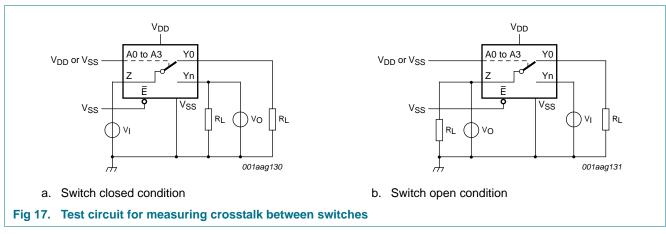


Fig 14. Test circuit for measuring frequency response







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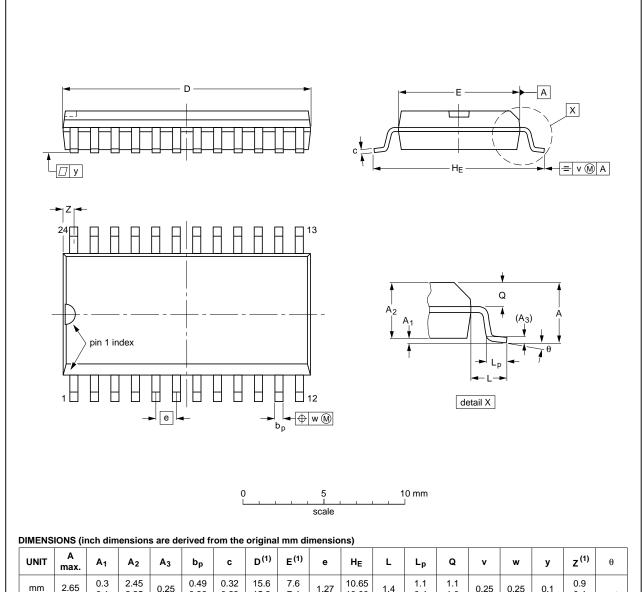
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# 12. Package outline

## SO24: plastic small outline package; 24 leads; body width 7.5 mm

SOT137-1



UNIT	A max.	A <sub>1</sub>	A <sub>2</sub>	А3	bp	С	D <sup>(1)</sup>	E <sup>(1)</sup>	е	HE	L	Lp	Q	٧	w	у	z <sup>(1)</sup>	θ
mm	2.65	0.3 0.1	2.45 2.25	0.25	0.49 0.36	0.32 0.23	15.6 15.2	7.6 7.4	1.27	10.65 10.00	1.4	1.1 0.4	1.1 1.0	0.25	0.25	0.1	0.9 0.4	8°
inches	0.1	0.012 0.004	0.096 0.089	0.01	0.019 0.014	0.013 0.009	0.61 0.60	0.30 0.29	0.05	0.419 0.394	0.055	0.043 0.016	0.043 0.039	0.01	0.01	0.004	0.035 0.016	0°

#### Note

1. Plastic or metal protrusions of 0.15 mm (0.006 inch) maximum per side are not included.

OUTLINE		REFER	EUROPEAN	ISSUE DATE			
VERSION	IEC	JEDEC	JEITA		PROJECTION	ISSUE DATE	
SOT137-1	075E05	MS-013				<del>99-12-27</del> 03-02-19	

Fig 18. Package outline SOT137-1 (SO24)

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# 13. Abbreviations

#### Table 13. Abbreviations

Acronym	Description
НВМ	Human Body Model
ESD	ElectroStatic Discharge
MM	Machine Model
MIL	Military

# 14. Revision history

## Table 14. Revision history

Document ID	Release date	Data sheet status	Change notice	Supersedes
HEF4067B-Q100 v.1	20130924	Product data sheet	-	-

## 15. Legal information

#### 15.1 Data sheet status

Document status[1][2]	Product status[3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
Product [short] data sheet	Production	This document contains the product specification.

- [1] Please consult the most recently issued document before initiating or completing a design.
- [2] The term 'short data sheet' is explained in section "Definitions"
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